200600 4691
23 Jan 06

162162

(12) INTERNATIONAL APPLICATION PUBLISHED UNDER THE PATENT COOPERATION TREATY (PCT)

(19) World Intellectual Property Organization
International Bureau

(43) International Publication Date
17 February 2005 (17.02.2005)

PCT

(10) International Publication Number
WO 2005/014896 A1

(51) International Patent Classification[7]: C30B 25/02, H01L 21/762, C30B 33/00

(21) International Application Number: PCT/EP2004/007578

(22) International Filing Date: 7 July 2004 (07.07.2004)

(25) Filing Language: English

(26) Publication Language: English

(30) Priority Data:
03 09079 24 July 2003 (24.07.2003) FR

(71) Applicant *(for all designated States except US)*: **S.O.I.TEC SILICON ON INSULATOR TECHNOLOGIES** [FR/FR]; Parc Technologique des Fontaines, Chemin des Franques, F-38190 Bernin (FR).

(72) Inventors; and

(75) Inventors/Applicants *(for US only)*: **LETERTRE, Fabrice** [FR/FR]; 33 Quai Jongkind, F-38000 Grenoble (FR). **FAURE, Bruce** [FR/FR]; 4 Place Claveyson, F-38000 Grenoble (FR).

(74) Agent: **CABINET REGIMBEAU**; Espace Performance, Bâtiment K, F-35769 Saint Grégoire Cedex (FR).

(81) Designated States *(unless otherwise indicated, for every kind of national protection available)*: AE, AG, AL, AM, AT, AU, AZ, BA, BB, BG, BR, BW, BY, BZ, CA, CH, CN, CO, CR, CU, CZ, DE, DK, DM, DZ, EC, EE, EG, ES, FI, GB, GD, GE, GH, GM, HR, HU, ID, IL, IN, IS, JP, KE, KG, KP, KR, KZ, LC, LK, LR, LS, LT, LU, LV, MA, MD, MG, MK, MN, MW, MX, MZ, NA, NI, NO, NZ, OM, PG, PH, PL, PT, RO, RU, SC, SD, SE, SG, SK, SL, SY, TJ, TM, TN, TR, TT, TZ, UA, UG, US, UZ, VC, VN, YU, ZA, ZM, ZW.

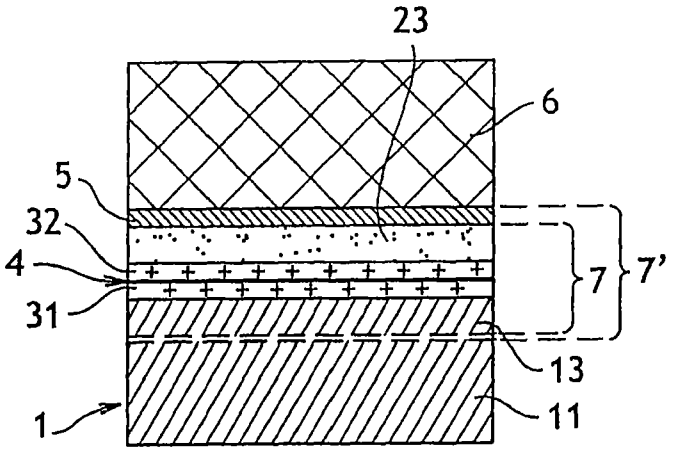
(84) Designated States *(unless otherwise indicated, for every kind of regional protection available)*: ARIPO (BW, GH, GM, KE, LS, MW, MZ, NA, SD, SL, SZ, TZ, UG, ZM, ZW), Eurasian (AM, AZ, BY, KG, KZ, MD, RU, TJ, TM), European (AT, BE, BG, CH, CY, CZ, DE, DK, EE, ES, FI, FR, GB, GR, HU, IE, IT, LU, MC, NL, PL, PT, RO, SE, SI, SK, TR), OAPI (BF, BJ, CF, CG, CI, CM, GA, GN, GQ, GW, ML, MR, NE, SN, TD, TG).

Published:
— *with international search report*

For two-letter codes and other abbreviations, refer to the "Guidance Notes on Codes and Abbreviations" appearing at the beginning of each regular issue of the PCT Gazette.

23 JAN 2006

(54) Title: A METHOD OF FABRICATING AN EPITAXIALLY GROWN LAYER



(57) Abstract: The invention concerns a method of fabricating an epitaxially grown layer (6), an epitaxy support (9,9') and its method of fabricating. This method is remarkable in that it comprises the following steps consisting in : a) implanting atomic species within a support substrate (1) to define therein a zone of weakness which demarcates a thin support layer (13) from the remainder (11) of said substrate ; b) transferring onto said thin layer (13) a thin nucleation layer (23) ; c) detaching said remainder (11) along said zone of weakness, but while maintaining the thin support layer (13) in contact with said remainder (11) ; d) growing said epitaxially grown layer (6) by epitaxy on said nucleation layer (23); and e) moving away the remainder (11) from the thin support layer (13). Application to the field of optics, opto-electronics, or electronics.

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